



Excellence in Electronics

TYPE 1N460

The 1N460 is a hermetically sealed silicon junction diode designed for general purpose applications and providing extreme stability, wide temperature range, high back resistance (100 megohms or more), and high ratio of back to forward resistance. The flexible terminal leads may be soldered or welded directly to the terminals of circuit components without the use of sockets. Standard in-line subminiature sockets may be used by cutting the leads to a suitable length.

MECHANICAL DATA

CASE: Metal and Glass

BASE: None (0.020" tinned kovar wire. Length: 1.5" min. Spacing: 0.080" center-to-center)

TERMINAL CONNECTIONS: (Black Dot is adjacent to Cathode Terminal)

MOUNTING POSITION: Any

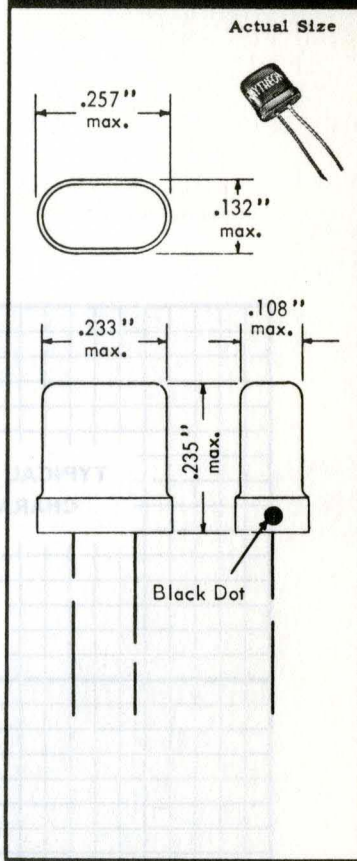
ELECTRICAL DATA

RATINGS - ABSOLUTE MAXIMUM VALUES: (at 25°C)

Peak Inverse Voltage	90 volts
Continuous Inverse Voltage	85 volts
Average Rectified Current	40 ma.
Average Rectified Current (100°C)	25 ma.
Peak Rectified Current	120 ma.
Surge Current (for 1 sec.)	130 ma.
Ambient Temperature Range	-55 to +150 °C
Dissipations at:	
25°C	150 mw.
65°C	110 mw.
100°C	75 mw.
150°C	25 mw.

CHARACTERISTICS:

	100°C	25°C
Maximum Inverse Current at -10 volts	0.2	0.01 μa.
Maximum Inverse Current at -75 volts	----	0.1 μa.
Minimum Forward Current at +1.0 volt	----	5 ma.



Tentative Data

RAYTHEON MANUFACTURING COMPANY

RECEIVING AND CATHODE RAY TUBE OPERATIONS



SILICON JUNCTION DIODE

The 1N460 is a technically evolved silicon junction diode designed for general purpose applications and providing extreme reliability with temperature range, high peak resistance (100 megohms) to make it well suited to back-to-back applications. The flexible terminal leads may be retained or welded directly to the terminals of circuit components without the use of solder. Standard in-line substitutive sockets may be used by cutting the leads to a suitable length.

